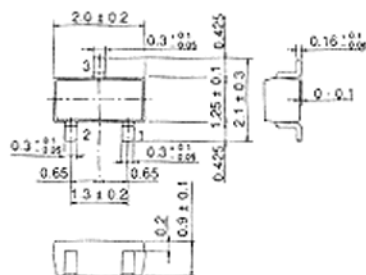


2SC4263

SILICON NPN EPITAXIAL

VHF RF AMPLIFIER



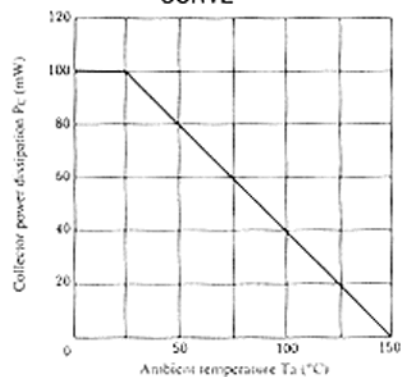
1. Emitter
 2. Base
 3. Collector
- (Dimensions in mm)

(CMPAK)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SC4263	Unit
Collector to base voltage	V_{CBO}	15	V
Collector to emitter voltage	V_{CEO}	12	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_C	20	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	15	—	—	V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1mA, R_{BE} = \infty$	12	—	—	V
Collector cutoff current	I_{CBO}	$V_{CB} = 12V, I_E = 0$	—	—	0.3	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 3V, I_C = 0$	—	—	10	μA
DC current transfer ratio	h_{FE}	$V_{CE} = 4V, I_C = 2mA$	30	—	200	
Reverse transfer capacitance	C_{re}	$V_{CB} = 4V, I_C = 0, f = 1MHz,$ Emitter Common	—	0.3	0.5	pF
Gain bandwidth product	f_T	$V_{CE} = 4V, I_C = 2mA$	700	1000	—	MHz
Power gain	PG	$V_{CC} = 6V, I_C = 2mA, f = 200MHz$	16	—	—	dB
Noise figure	NF		—	—	3.2	dB
AGC voltage	V_{AGC}	$V_{CC} = 6V, GR = 30dB, f = 200MHz$	2.4	—	3.6	V

• Marking is [1L-].

■ See characteristic curves of 2SC2727.